

MOSFET

PG-TO220-3

StrongIRFET™ 2 Power-Transistor, 100 V

Features

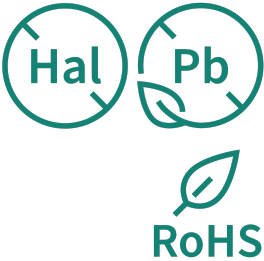
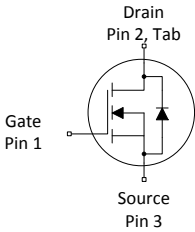
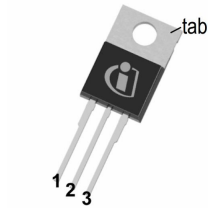
- Optimized for a wide range of applications
- N-channel, normal level
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified according to JEDEC Standard

Table 1 Key performance parameters

| Parameter        | Value | Unit |
|------------------|-------|------|
| $V_{DS}$         | 100   | V    |
| $R_{DS(on),max}$ | 3.0   | mΩ   |
| $I_D$            | 179   | A    |
| $Q_{oss}$        | 109   | nC   |
| $Q_G$            | 85    | nC   |



| Part number   | Package    | Marking  | Related links |
|---------------|------------|----------|---------------|
| IPP030N10NF2S | PG-TO220-3 | 030N10NS | -             |



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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                    | Symbol            | Values |      |                         | Unit | Note / Test condition                                                                                                                                                                                                       |
|----------------------------------------------|-------------------|--------|------|-------------------------|------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                                              |                   | Min.   | Typ. | Max.                    |      |                                                                                                                                                                                                                             |
| Continuous drain current <sup>1)</sup>       | $I_D$             | -      | -    | 179<br>137<br>129<br>25 | A    | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=6\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=40\text{ °C/W}$ <sup>2)</sup> |
| Pulsed drain current <sup>3)</sup>           | $I_{D,pulse}$     | -      | -    | 716                     | A    | $T_A=25\text{ °C}$                                                                                                                                                                                                          |
| Avalanche energy, single pulse <sup>4)</sup> | $E_{AS}$          | -      | -    | 367                     | mJ   | $I_D=80\text{ A}$ , $R_{GS}=25\text{ }\Omega$                                                                                                                                                                               |
| Gate source voltage                          | $V_{GS}$          | -20    | -    | 20                      | V    | -                                                                                                                                                                                                                           |
| Power dissipation                            | $P_{tot}$         | -      | -    | 250<br>3.8              | W    | $T_C=25\text{ °C}$<br>$T_A=25\text{ °C}$ , $R_{thJA}=40\text{ °C/W}$ <sup>2)</sup>                                                                                                                                          |
| Operating and storage temperature            | $T_j$ , $T_{stg}$ | -55    | -    | 175                     | °C   | -                                                                                                                                                                                                                           |

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information

<sup>4)</sup> See Diagram 13 for more detailed information

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter                                                                               | Symbol     | Values |      |      | Unit | Note / Test condition |
|-----------------------------------------------------------------------------------------|------------|--------|------|------|------|-----------------------|
|                                                                                         |            | Min.   | Typ. | Max. |      |                       |
| Thermal resistance, junction - case                                                     | $R_{thJC}$ | -      | -    | 0.6  | °C/W | -                     |
| Thermal resistance, junction - ambient,<br>6 cm <sup>2</sup> cooling area <sup>5)</sup> | $R_{thJA}$ | -      | -    | 40   | °C/W |                       |
| Thermal resistance, junction - ambient,<br>minimal footprint                            | $R_{thJA}$ | -      | -    | 62   | °C/W |                       |

<sup>5)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

| Parameter                                      | Symbol        | Values |            |            | Unit          | Note / Test condition                                                                                                                 |
|------------------------------------------------|---------------|--------|------------|------------|---------------|---------------------------------------------------------------------------------------------------------------------------------------|
|                                                |               | Min.   | Typ.       | Max.       |               |                                                                                                                                       |
| Drain-source breakdown voltage                 | $V_{(BR)DSS}$ | 100    | -          | -          | V             | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$                                                                                               |
| Gate threshold voltage                         | $V_{GS(th)}$  | 2.2    | 3.0        | 3.8        | V             | $V_{DS}=V_{GS}$ , $I_D=140\text{ }\mu\text{A}$                                                                                        |
| Zero gate voltage drain current                | $I_{DSS}$     | -      | 0.1<br>10  | 1<br>100   | $\mu\text{A}$ | $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$<br>$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$ |
| Gate-source leakage current                    | $I_{GSS}$     | -      | 10         | 100        | nA            | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                                                                                            |
| Drain-source on-state resistance <sup>6)</sup> | $R_{DS(on)}$  | -      | 2.5<br>3.1 | 3.0<br>3.7 | m $\Omega$    | $V_{GS}=10\text{ V}$ , $I_D=80\text{ A}$<br>$V_{GS}=6\text{ V}$ , $I_D=40\text{ A}$                                                   |
| Gate resistance                                | $R_G$         | -      | 2.0        | -          | $\Omega$      | -                                                                                                                                     |
| Transconductance <sup>7)</sup>                 | $g_{fs}$      | 85     | 170        | -          | S             | $ V_{DS} \geq 2 I_D R_{DS(on)max}$ , $I_D=80\text{ A}$                                                                                |

<sup>6)</sup>  $R_{DS(on)}$  is specified at a distance of 1.8 mm distance to the package body; mounting at a larger distance increases the overall package resistance of approximately 0.04 mOhm/mm per leg.

<sup>7)</sup> Defined by design. Not subject to production test.

**Table 5 Dynamic characteristics**

| Parameter                    | Symbol       | Values |      |      | Unit | Note / Test condition                                                                              |
|------------------------------|--------------|--------|------|------|------|----------------------------------------------------------------------------------------------------|
|                              |              | Min.   | Typ. | Max. |      |                                                                                                    |
| Input capacitance            | $C_{iss}$    | -      | 6000 | -    | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$                                      |
| Output capacitance           | $C_{oss}$    | -      | 930  | -    | pF   |                                                                                                    |
| Reverse transfer capacitance | $C_{rss}$    | -      | 41   | -    | pF   |                                                                                                    |
| Turn-on delay time           | $t_{d(on)}$  | -      | 19   | -    | ns   | $V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=80\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Rise time                    | $t_r$        | -      | 20   | -    | ns   |                                                                                                    |
| Turn-off delay time          | $t_{d(off)}$ | -      | 40   | -    | ns   |                                                                                                    |
| Fall time                    | $t_f$        | -      | 17   | -    | ns   |                                                                                                    |

**Table 6 Gate charge characteristics** <sup>8)</sup>

| Parameter                       | Symbol        | Values |      |      | Unit | Note / Test condition                                                       |
|---------------------------------|---------------|--------|------|------|------|-----------------------------------------------------------------------------|
|                                 |               | Min.   | Typ. | Max. |      |                                                                             |
| Gate to source charge           | $Q_{gs}$      | -      | 28   | -    | nC   | $V_{DD}=50\text{ V}$ , $I_D=80\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate charge at threshold        | $Q_{g(th)}$   | -      | 18.1 | -    | nC   |                                                                             |
| Gate to drain charge            | $Q_{gd}$      | -      | 17.4 | -    | nC   |                                                                             |
| Switching charge                | $Q_{sw}$      | -      | 27   | -    | nC   |                                                                             |
| Gate charge total <sup>9)</sup> | $Q_g$         | -      | 85   | 127  | nC   |                                                                             |
| Gate plateau voltage            | $V_{plateau}$ | -      | 4.6  | -    | V    | $V_{DS}=50\text{ V}$ , $V_{GS}=0\text{ V}$                                  |
| Output charge                   | $Q_{oss}$     | -      | 109  | -    | nC   |                                                                             |

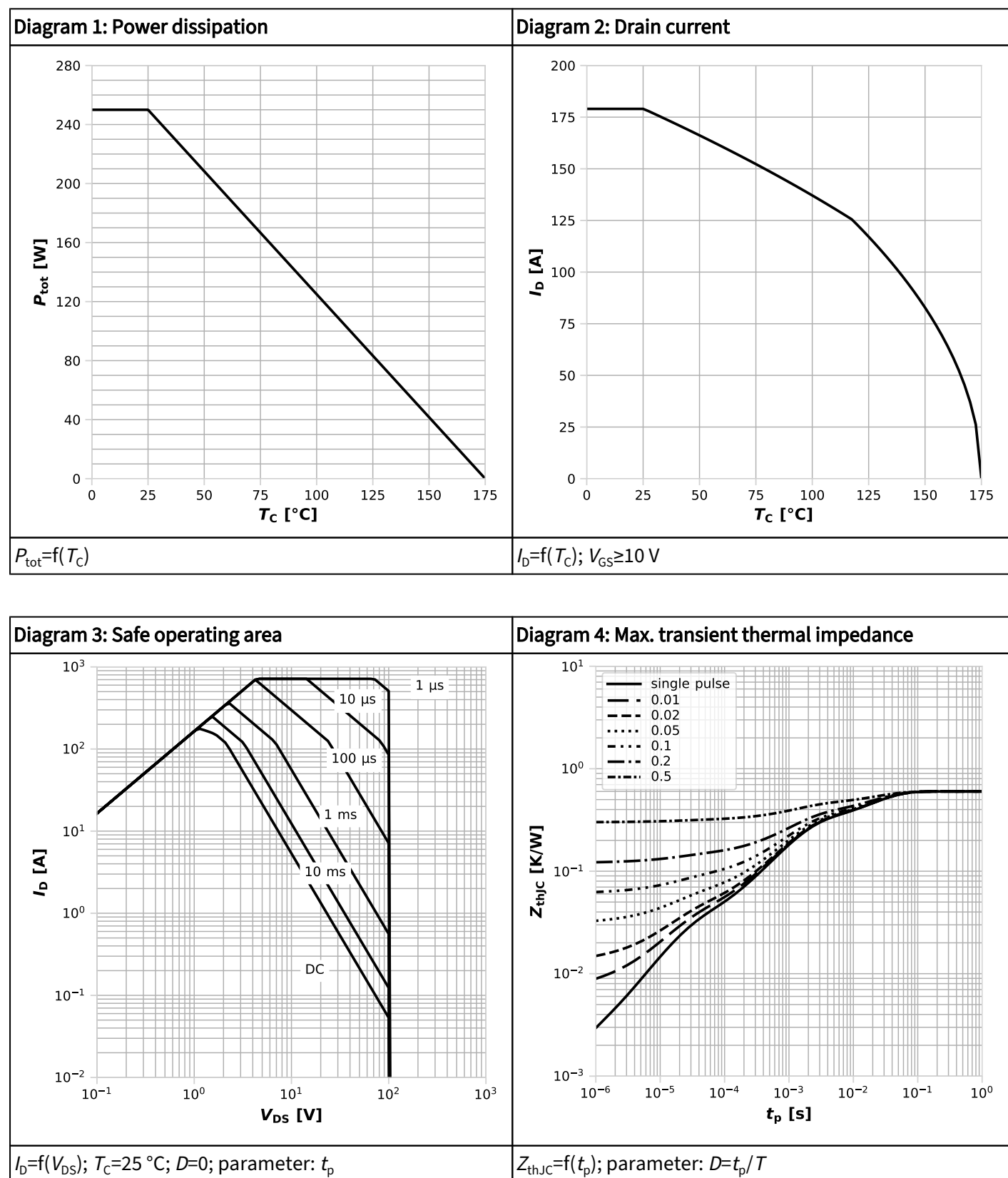
<sup>8)</sup> See "Gate charge waveforms" for parameter definition

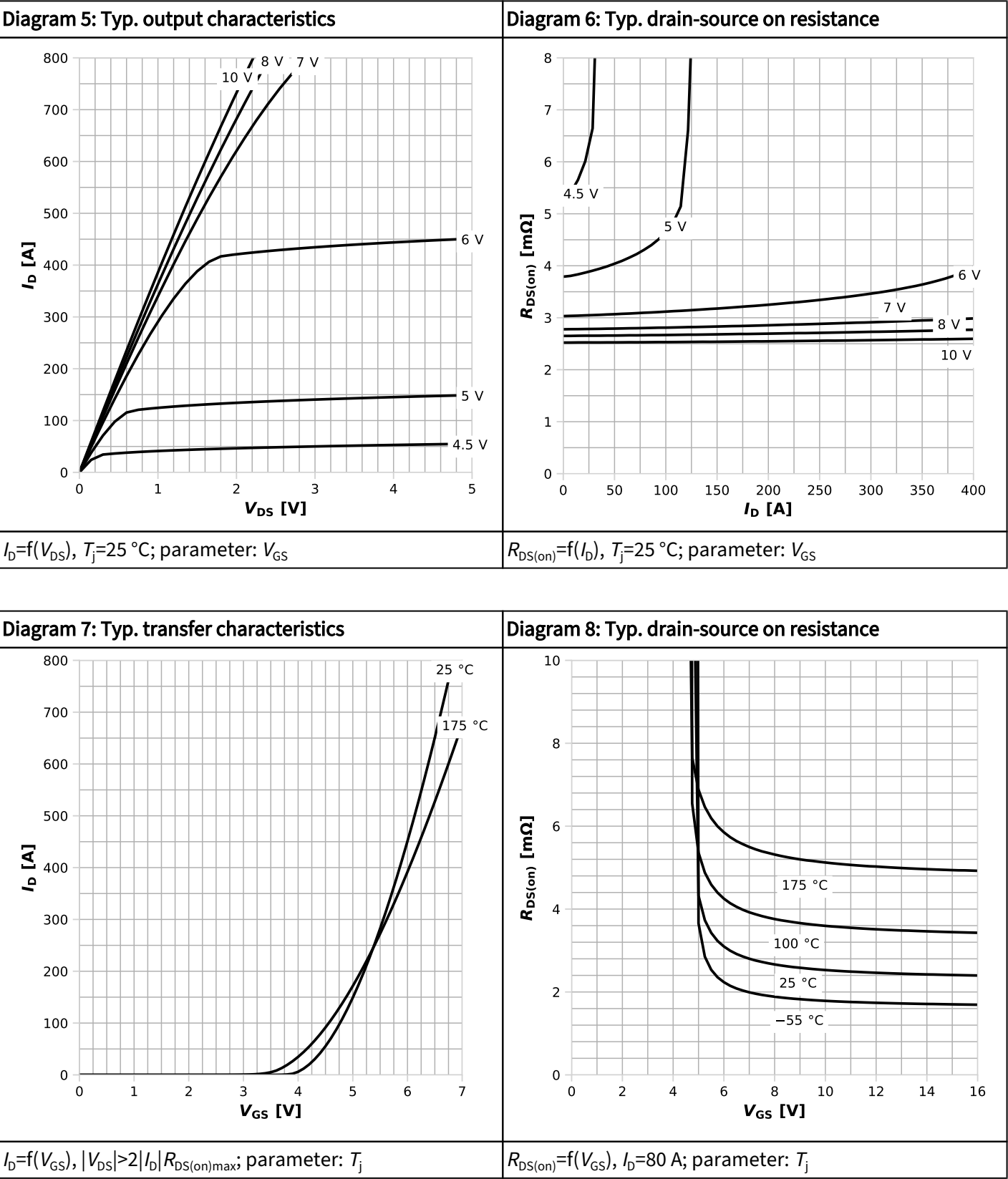
<sup>9)</sup> Defined by design. Not subject to production test.

**Table 7 Reverse diode**

| Parameter                        | Symbol        | Values |      |      | Unit | Note / Test condition                                                      |
|----------------------------------|---------------|--------|------|------|------|----------------------------------------------------------------------------|
|                                  |               | Min.   | Typ. | Max. |      |                                                                            |
| Diode continuous forward current | $I_S$         | -      | -    | 151  | A    | $T_C=25\text{ °C}$                                                         |
| Diode pulse current              | $I_{S,pulse}$ | -      | -    | 716  | A    |                                                                            |
| Diode forward voltage            | $V_{SD}$      | -      | 0.88 | 1.2  | V    | $V_{GS}=0\text{ V}$ , $I_F=80\text{ A}$ , $T_J=25\text{ °C}$               |
| Reverse recovery time            | $t_{rr}$      | -      | 37   | -    | ns   | $V_R=50\text{ V}$ , $I_F=80\text{ A}$ , $di_F/dt=500\text{ A}/\mu\text{s}$ |
| Reverse recovery charge          | $Q_{rr}$      | -      | 257  | -    | nC   |                                                                            |

## 4 Electrical characteristics diagrams





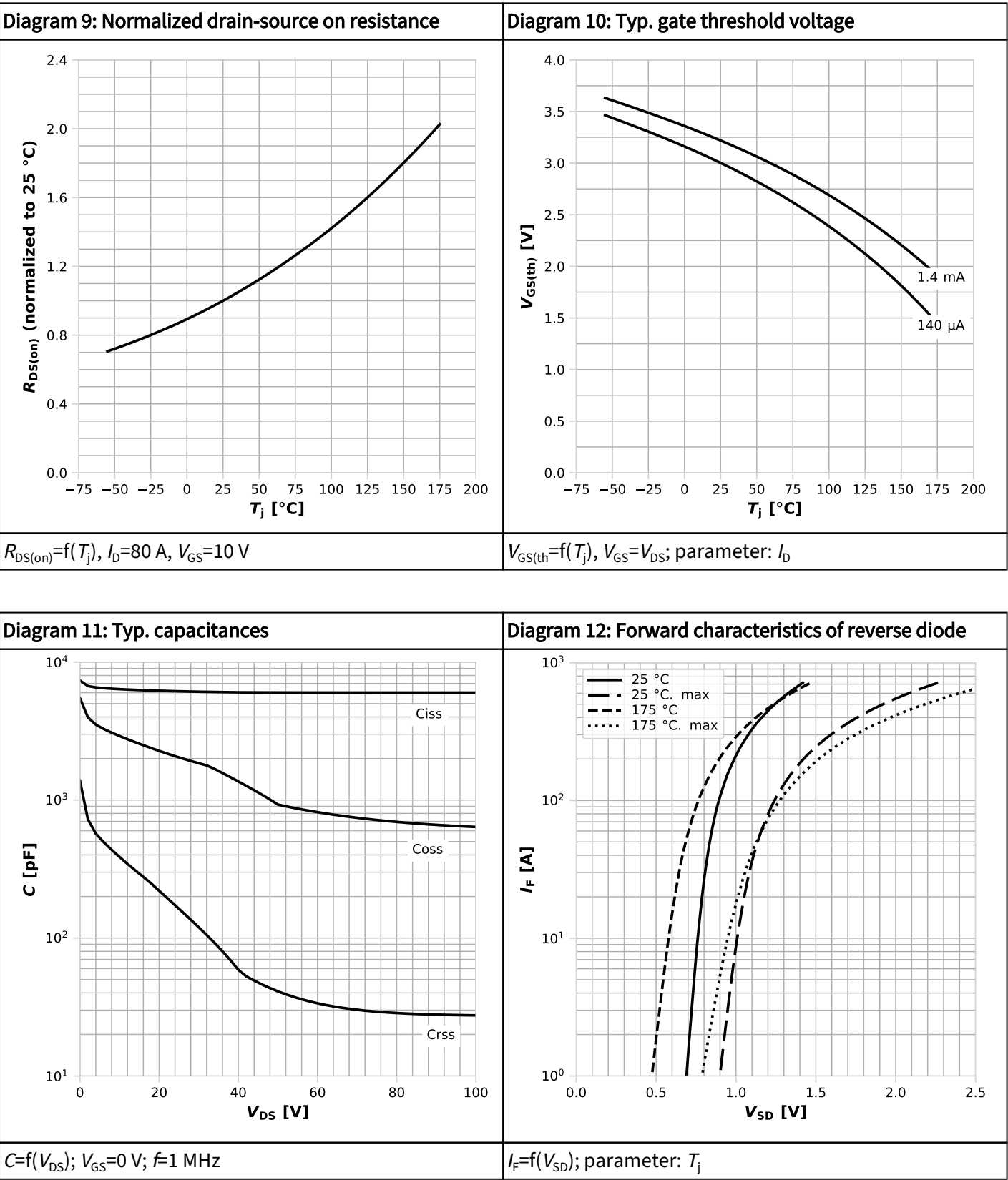
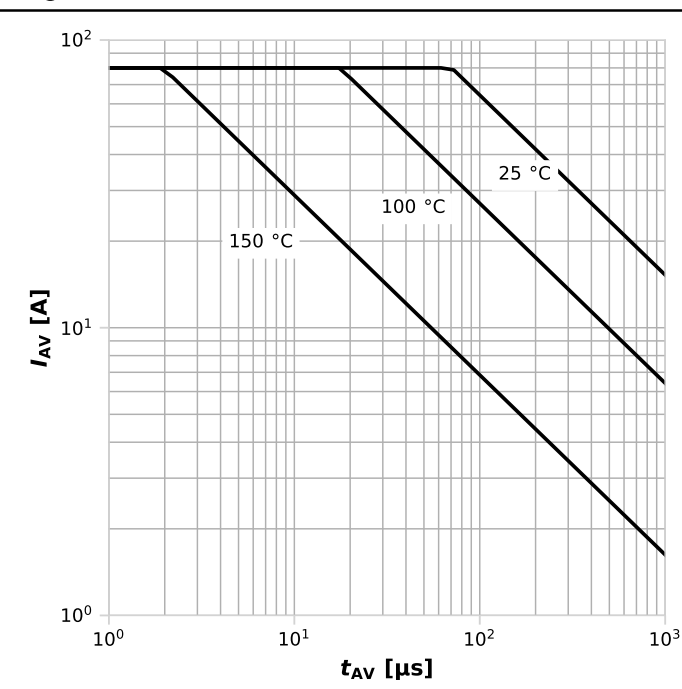


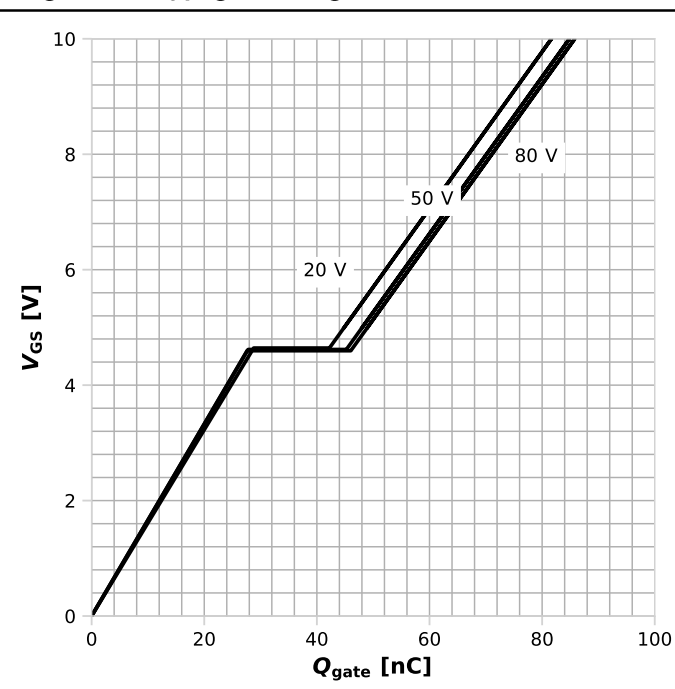


Diagram 13: Avalanche characteristics



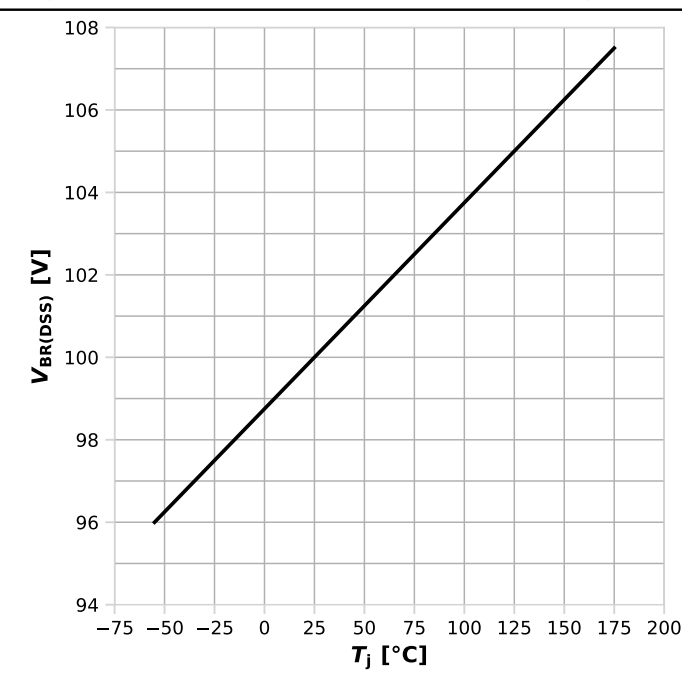
$I_{AS}=f(t_{AV})$ ;  $R_{GS}=25\ \Omega$ ; parameter:  $T_{j,start}$

Diagram 14: Typ. gate charge



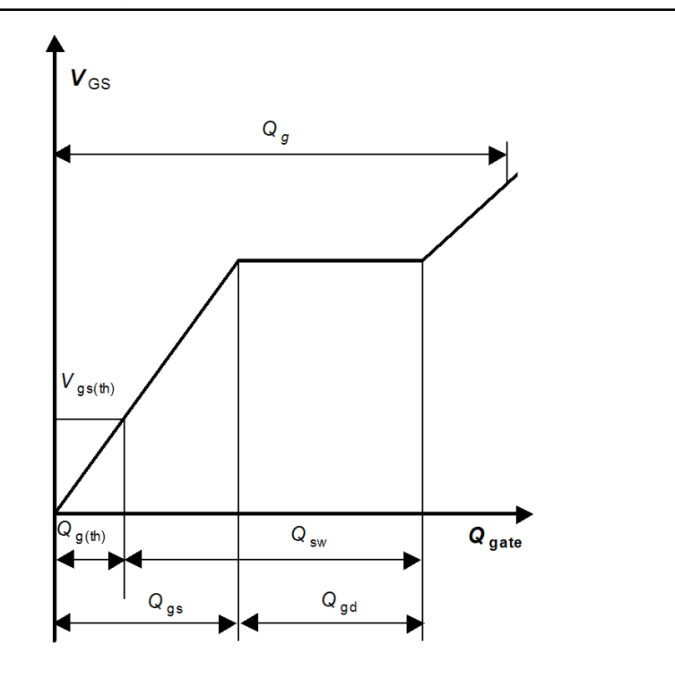
$V_{GS}=f(Q_{gate})$ ,  $I_D=80\text{ A}$  pulsed,  $T_j=25\text{ °C}$ ; parameter:  $V_{DD}$

Diagram 15: Min. drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$ ;  $I_D=1\text{ mA}$

Gate charge waveforms



5 Package outlines

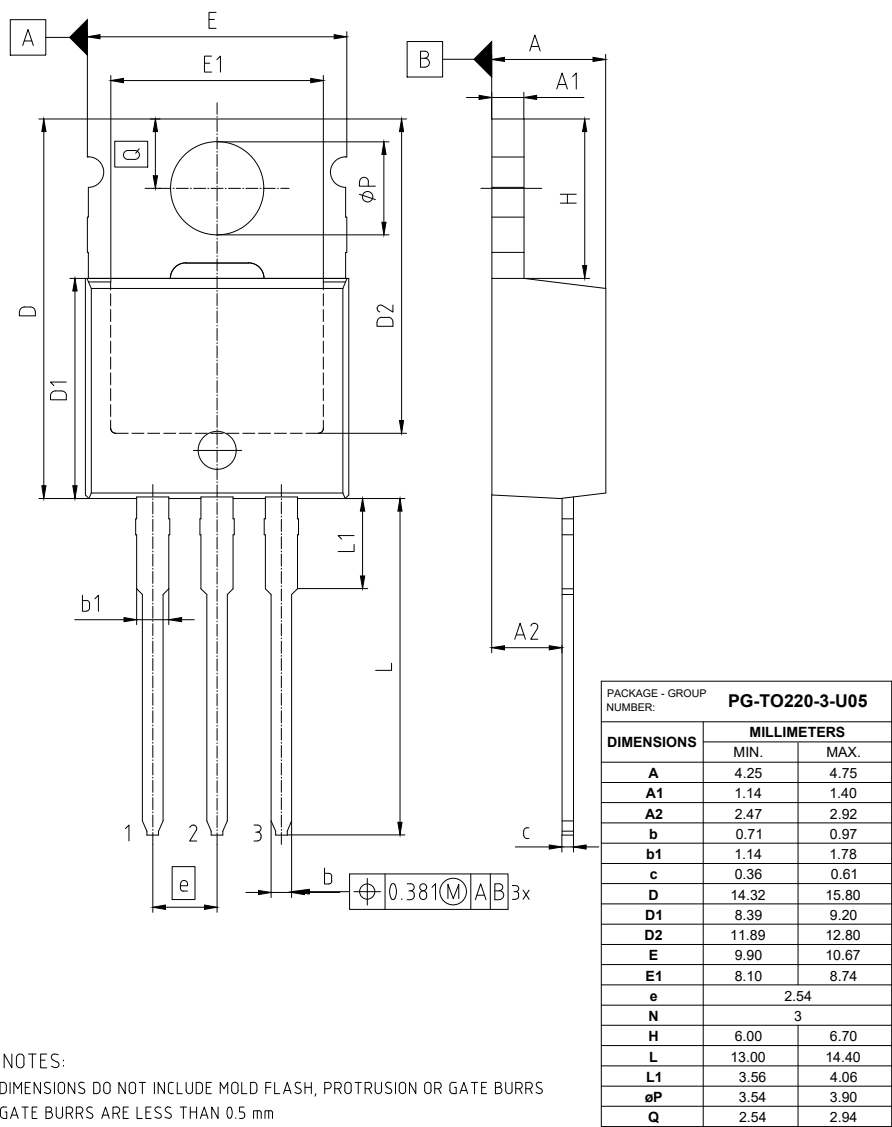


Figure 1 Outline PG-TO220-3, dimensions in mm

## Revision history

IPP030N10NF2S

### Revision 2025-01-20, Rev. 1.0

Previous revisions

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|----------------------------------------------|
| 1.0      | 2025-01-20 | Release of final datasheet                   |

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